



A1A:100.XX

VOLTAGE RATINGS

Part Number	V _{RRM} , V _R (V)		Max. rep. peak reverse voltage	V _{RSM} , V _R (V)	Max. non-rep. peak reverse voltage
	T _J = 0 to 180°C	T _J = -40 to 0°C			
A1A:100.02	200	200		300	
A1A:100.04	400	400		500	
A1A:100.06	600	600		700	
A1A:100.08	800	800		900	
A1A:100.10	1000	1000		1100	
A1A:100.12	1200	1200		1300	
A1A:100.14	1400	1400		1500	
A1A:100.16	1600	1600		1700	

This datasheet applies to:

**Metric thread: A1A:100.XX,
A1B:100.XX**

**Inch thread: A2A:100.XX,
A2B:100.XX**

MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES
T _J Junction Temperature	-40 to 180	°C	-
T _{stg} Storage Temperature	-40 to 180	°C	-
I _{F(AV)} Max. Av. current	100	A	180° half sine wave
@ Max. T _C	125	°C	
I _{F(RMS)} Nom. RMS current	200	A	-
I _{FSM} Max. Peak non-rep. surge current	1000 1200 1500 1650	A	50 Hz half cycle sine wave 60 Hz half cycle sine wave 50 Hz half cycle sine wave 60 Hz half cycle sine wave Initial T _J = 180°C, rated V _{RRM} applied after surge. Initial T _J = 180°C, no voltage applied after surge.
I ² t Max. I ² t capability	8050 8775 11500 12535	A ² s	t = 10ms t = 8.3 ms t = 10ms t = 8.3 ms Initial T _J = 180°C, rated V _{RRM} applied after surge. Initial T _J = 180°C, no voltage applied after surge.
I ² t ^{1/2} Max. I ² t ^{1/2} capability	805000	A ² s ^{1/2}	Initial T _J = 180°C, no voltage applied after surge. for time t _x = I ² t ^{1/2} * t _x ^{1/2} . (0.1 < t _x < 10ms). It
F Mounting Force	10(~89)	N.m(Lbf.in)	-



A1A:100.XX

CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
V_{FM} Peak forward voltage	---	---	1.55	V	Initial $T_J = 25^\circ\text{C}$, sinusoidal wave, $I_{peak} = 314\text{A}$.
$V_{F(TO)}$ Threshold voltage	---	---	0.85	V	$T_J = 180^\circ\text{C}$, Av. Power = $V_{F(TO)} * I_{F(AV)} + r_F * [I_{F(RMS)}]^2$, sine.
r_F Forward slope resistance	---	---	1.80	m	Use low values for $I_{FM} < I_{F(AV)}$
I_{RM} Peak reverse current	---	10	15.00	mA	$T_J = 180^\circ\text{C}$. Max. Rated V_{RRM}
R_{thJC} Thermal resistance, junction-to-case	---	---	0.35	°C/W	DC operation
	---	---	0.40	°C/W	180° sine wave
	---	---	0.43	°C/W	120° rectangular wave
R_{thCS} Thermal resistance, case-to-sink	---	---	0.08	°C/W	Mtg. Surface smooth, flat and greased. Single side.
wt Weight	---	100(3.5)	---	g(oz.)	---
Case Style	DO-205AA (DO-8)		JEDEC		---

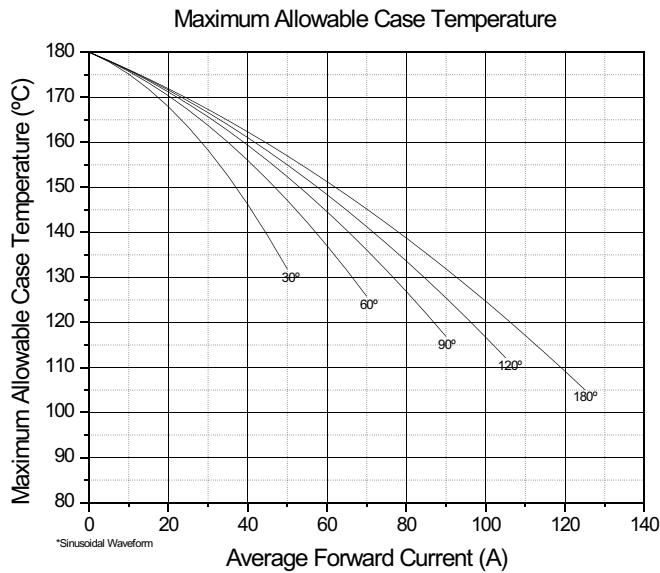


Fig. 1 - Current Ratings Characteristics

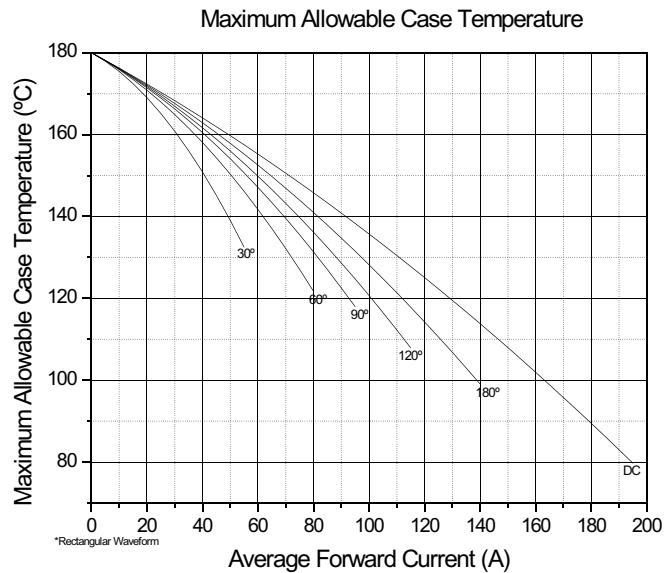


Fig. 2 - Current Ratings Characteristics



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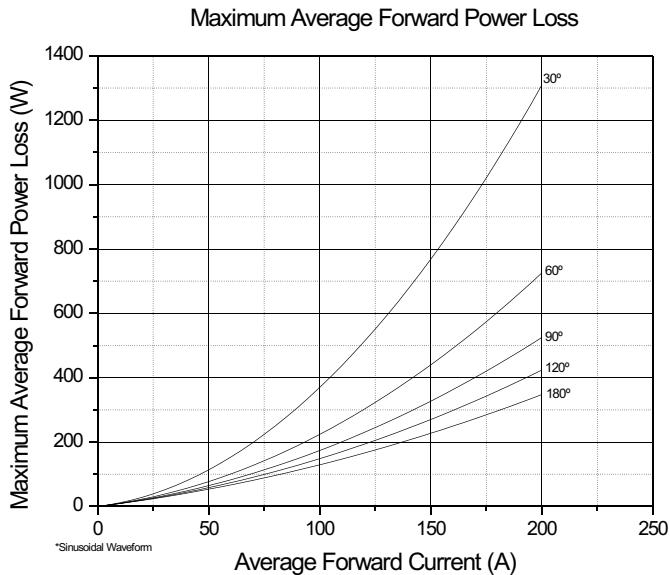


Fig. 3 - Forward Power Loss Characteristics

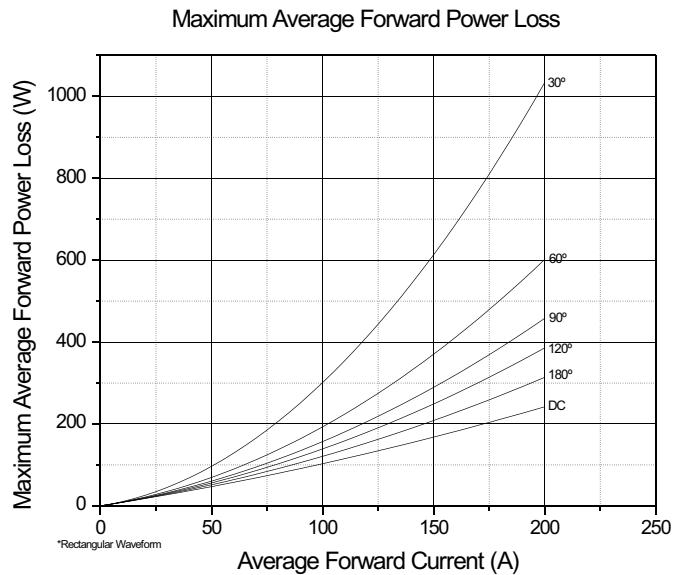


Fig. 4 - Forward Power Loss Characteristics

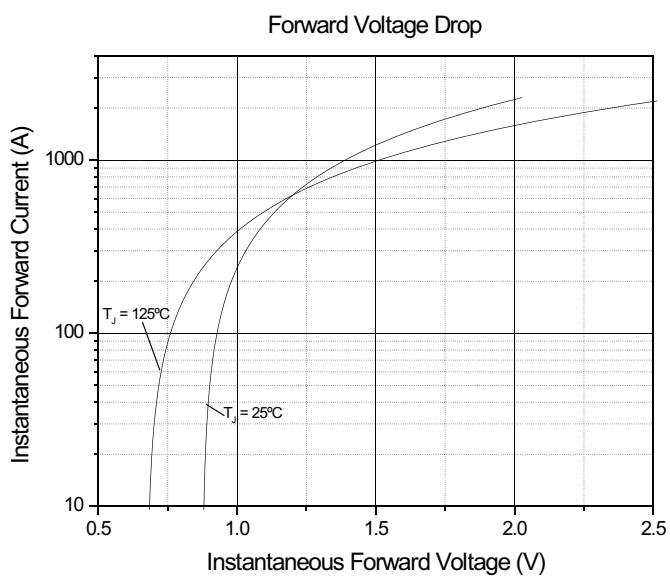


Fig. 5 - Forward Voltage Drop Characteristics

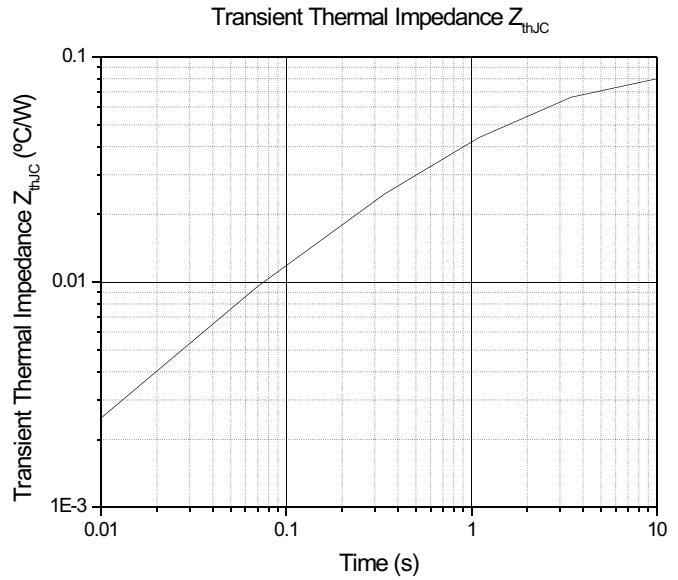


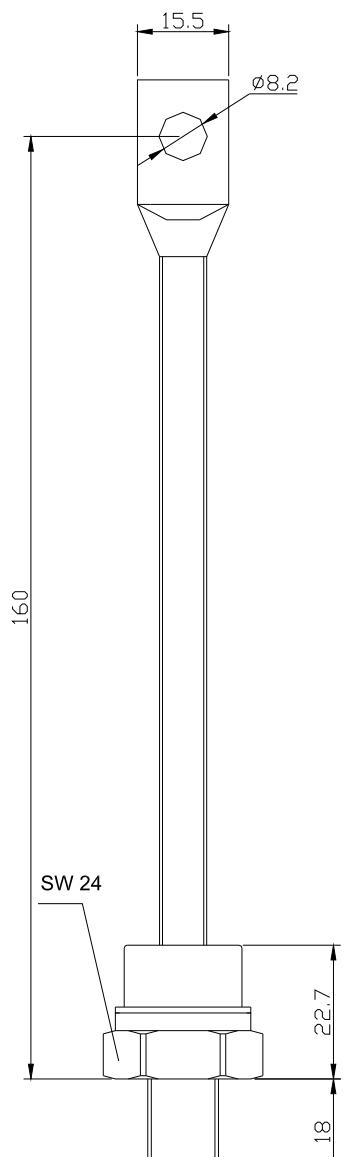
Fig. 6 - Transient Thermal Impedance Characteristics



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A1A:100.XX

DO-205AA (DO-8)



M12 x 1.75
1/2" UNF 2A